TOSHIBA Transistor Silicon NPN Triple Diffused Type (PCT process)

2SC4497

High Voltage Control Applications

• High voltage: $V_{CBO} = 300 \text{ V}$, $V_{CEO} = 300 \text{ V}$

• Low saturation voltage: VCE (sat) = 0.5 V (max)

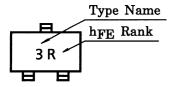
• Small collector output capacitance: Cob = 3 pF (typ.)

• Complementary to 2SA1721

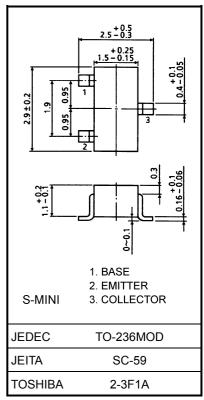
Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit	
Collector-base voltage	V_{CBO}	300	V	
Collector-emitter voltage	V_{CEO}	300	V	
Emitter-base voltage	V _{EBO}	6	V	
Collector current	IC	100	mA	
Base current	Ι _Β	20	mA	
Collector power dissipation	PC	200	mW	
Junction temperature	Tj	150	°C	
Storage temperature range	T _{stg}	-55~150	°C	

Marking



Unit: mm



Weight: 0.012 g (typ.)

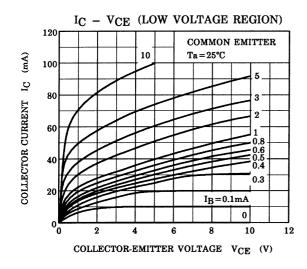


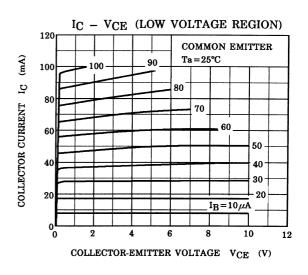
Electrical Characteristics (Ta = 25° C)

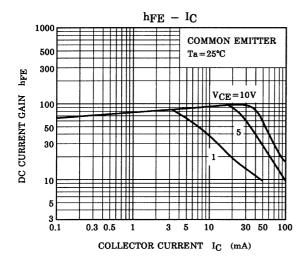
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	$V_{CB} = 300 \text{ V}, I_E = 0$	_	_	0.1	μΑ
Emitter cut-off current	I _{EBO}	V _{EB} = 6 V, I _C = 0	_	_	0.1	μА
Collector-base breakdown voltage	V (BR) CBO	$I_C = 0.1 \text{ mA}, I_E = 0$	300	_	_	V
Collector-emitter breakdown voltage	V _(BR) CEO	$I_C = 1 \text{ mA}, I_B = 0$	300	_	_	V
DC current gain	h _{FE (1)} (Note)	V _{CE} = 10 V, I _C = 20 mA	30	_	150	
	h _{FE (2)}	V _{CE} = 10 V, I _C = 1 mA	20	_	_	
Collector-emitter saturation voltage	V _{CE (sat)}	$I_C = 20 \text{ mA}, I_B = 2 \text{ mA}$	_	_	0.5	V
Base-emitter saturation voltage	V _{BE (sat)}	$I_C = 20 \text{ mA}, I_B = 2 \text{ mA}$	_	_	1.2	V
Transition frequency	f _T	V _{CE} = 10 V, I _C = 10 mA	_	70	_	MHz
Collector output capacitance	C _{ob}	V _{CB} = 20 V, I _E = 0, f = 1 MHz	_	3	4	pF

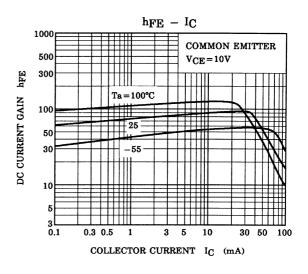
Note: $h_{FE (1)}$ classification R: 30~90, O: 50~150

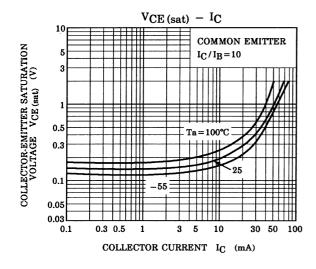
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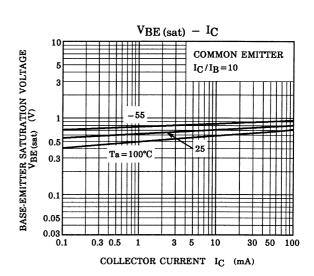




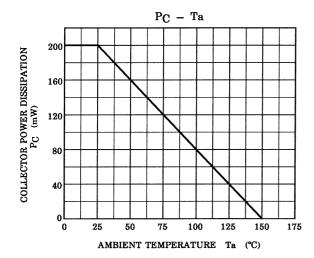








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